

# MOSFET 50N06

产品名称	MOSFET 50N06
公司名称	天津瀚金盛芯科技有限公司
价格	.00/个
规格参数	品牌:HJSX 型号:50N06 种类:绝缘栅(MOSFET)
公司地址	南开区城厢中路与北城街交口西北侧尚佳新苑5-1-707
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## 产品详情

品牌	HJSX	型号	50N06
种类	绝缘栅(MOSFET)	沟道类型	N沟道
导电方式	增强型	用途	TR/激励、驱动
封装外形	WAFER/裸芯片	材料	N-FET硅N沟道
开启电压	= ( V )	夹断电压	= ( V )
跨导	= ( $\mu$ S )	极间电容	= ( pF )
低频噪声系数	= ( dB )	最大漏极电流	= ( mA )
最大耗散功率	= ( mW )		

50 amps , 60voltsn-channel mosfet descriptionthe 50n06 is a n-channel enhancement mosfet and is designed to havebetter characteristics, such as superior switching performance, and withstandhigh energy pulse in the avalanche and commutation mode. these devices arewell suited for low voltage applications such as automotive dc/dc converters,and high efficiency switching for power management in portable and batteryoperated products. features? rds(on)=0.023 @vgs=10v? low gate charge(typical 31nc)? low reverse transfer capacitance(crss=typical 80pf)? fast switching capability? avalanche energy specified? improved dv/dt capability,high ruggedness

absolute maximum ratings(tc=25 ,unless otherwise specified)parameter symbol ratings unitsdrain-source voltage vds 60 vgate-source voltage vgs  $\pm$  20 vtc=25 50 adrain current continuousid35 adrain current pulsed (note 1) idp 200 arepetitive (note 1) ear 13 mjalanche energy single pulse(note 2) eas 480 mjpeak diode recovery dv/dt(note 3) dv/dt 7.0 v/nstc=25 120 wtotal power dissipationderate above 25 pd0.8 w/ operation junction temperature tj -55 to+150 storage temperature tstg -55~+150